

Silicon NPN Power Transistors

2SC5297

DESCRIPTION

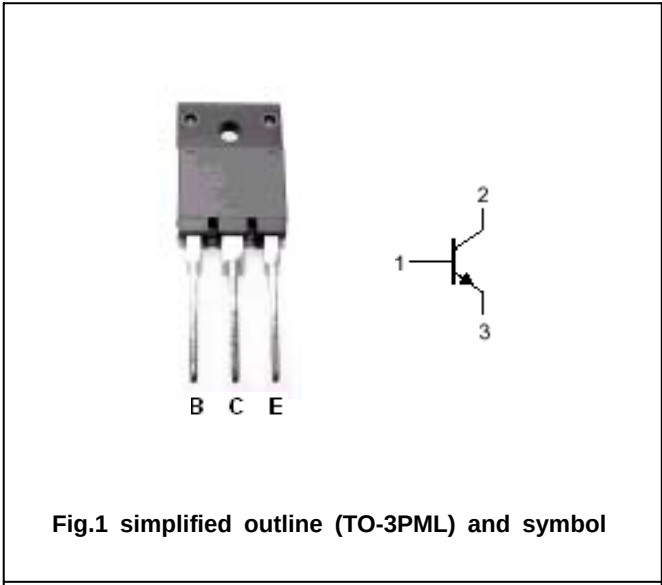
- With TO-3PML package
- High breakdown voltage, high reliability.
- High speed

APPLICATIONS

- Ultrahigh-definition CRT display
- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		16	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	60	W
			3	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

Silicon NPN Power Transistors

2SC5297

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A; I_B=1.25A$			5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A; I_B=1.25A$			1.5	V
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA; I_B=0$	800			V
I_{EBO}	Emitter cut-off current	$V_{EB}=4V; I_C=0$			1.0	mA
I_{CBO}	Collector cut-off current	$V_{CB}=800V; I_E=0$			10	μA
I_{CES}	Collector cut-off current	$V_{CE}=1500V; R_{BE}=0$			1	mA
h_{FE-1}	DC current gain	$I_C=1A; V_{CE}=5V$	20		30	
h_{FE-2}	DC current gain	$I_C=5A; V_{CE}=5V$	4		7	
Switching times						
t_{stg}	Storage time	$I_C=4A; R_L=50\Omega$ $I_{B1}=0.8A; I_{B2}=-1.6A$ $V_{CC}=200V$			3.0	μs
t_f	Fall time			0.1	0.2	μs

Silicon NPN Power Transistors

2SC5297

PACKAGE OUTLINE

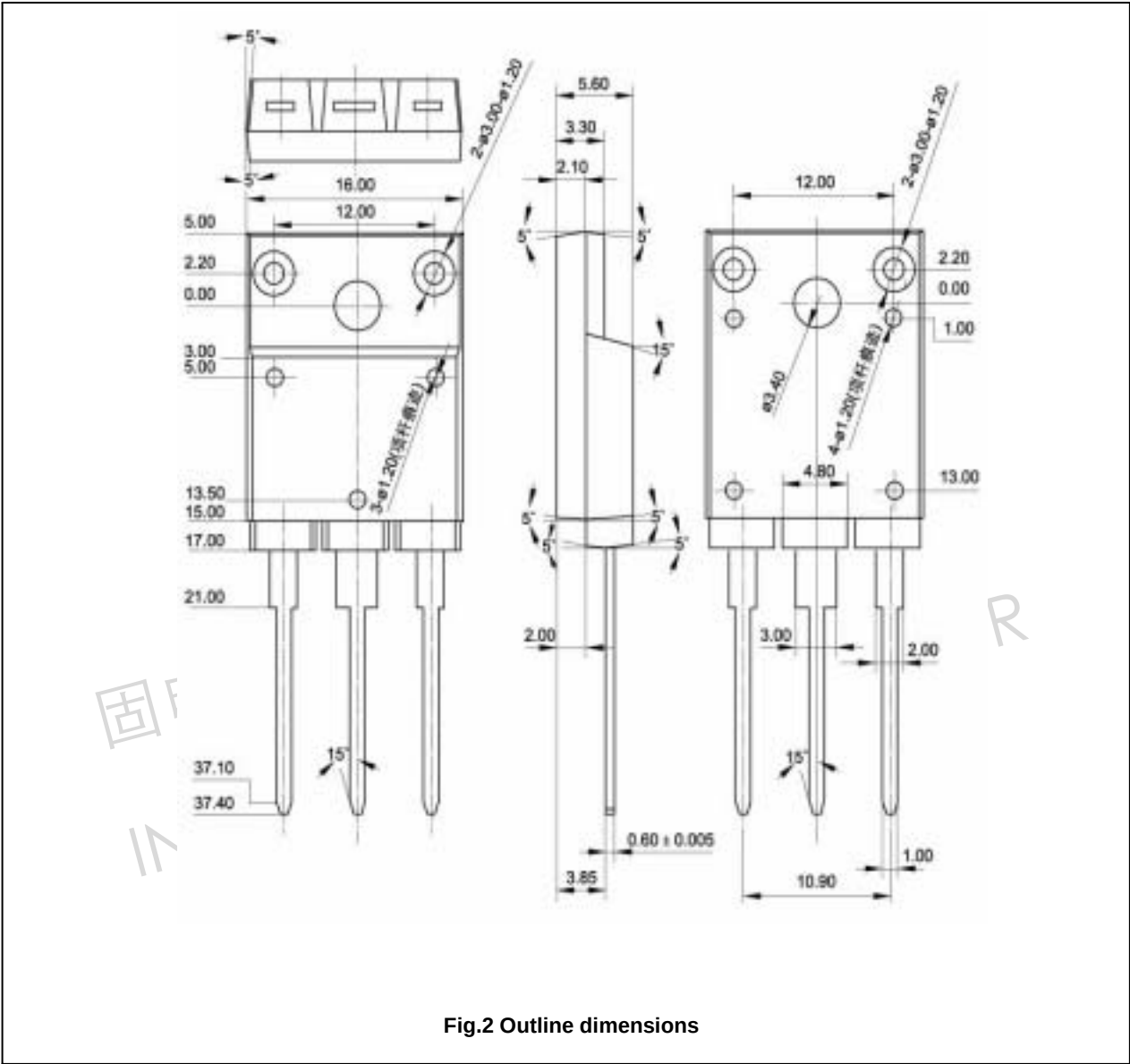


Fig.2 Outline dimensions

Silicon NPN Power Transistors

2SC5297

